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Team Nexperia



PBHV9115X

150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor
Rev. 01 — 10 March 2010 Product dat

Product data sheet

Product profile 1.

1.1 General description

PNP high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62/TO-243) small and flat Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C

1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-150	V
I _C	collector current		-	-	-1	Α
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V};$ $I_{C} = -50 \text{ mA}$	100	220	-	

Pinning information 2.

Table 2. **Pinning**

Pin	Description	Simplified outline	Graphic symbol
1	emitter		_
2	collector		2 J
3	base	3 2 1	3 — 1 sym079



150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

3. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PBHV9115X	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89				

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV9115X	*4G

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-200	V
V_{CEO}	collector-emitter voltage	open base	-	-150	V
V _{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-200	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-1	А
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-2	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	-400	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u>	520	mW
			[2]	1.5	W
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^{* =} p: made in Hong Kong

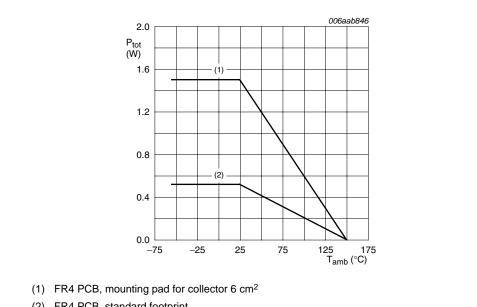
^{* =} t: made in Malaysia

^{* =} W: made in China

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².

PBHV9115X NXP Semiconductors

150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor



- (2) FR4 PCB, standard footprint

Fig 1. **Power derating curves**

Thermal characteristics 6.

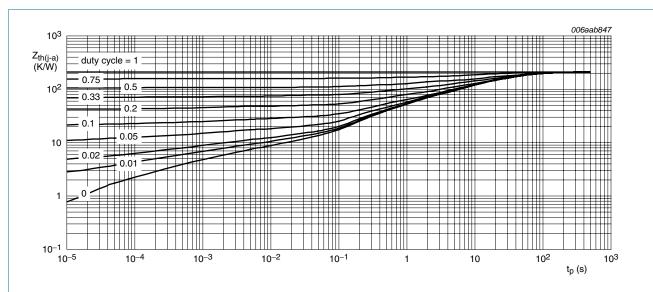
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	240	K/W
			[2] _	-	80	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	20	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

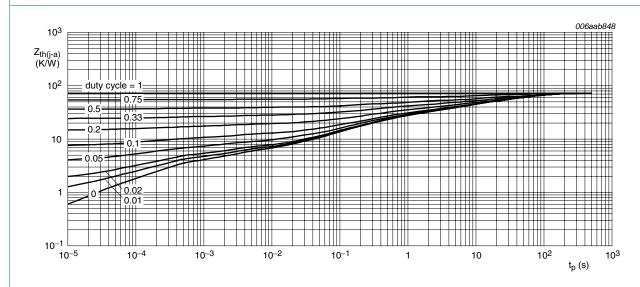
^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².

150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

7. Characteristics

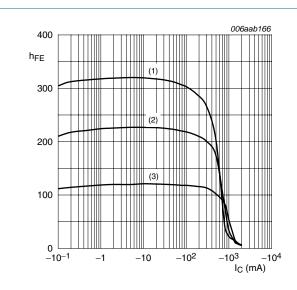
Table 7. Characteristics

 $T_{amb} = 25 \, ^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -120 \text{ V};$ $I_E = 0 \text{ A}$		-	-	-100	nA
		$V_{CB} = -120 \text{ V};$ $I_E = 0 \text{ A}; T_j = 150 \text{ °C}$		-	-	-10	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -120 \text{ V};$ $V_{BE} = 0 \text{ V}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -4 \text{ V; } I_{C} = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V}$					
		$I_C = -50 \text{ mA}$		100	220	-	
		$I_C = -100 \text{ mA}$	[1]	100	220	-	
		$I_C = -1 A$	[1]	10	30	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100 \text{ mA};$ $I_B = -10 \text{ mA}$	[1]	-	-60	-120	mV
		$I_C = -100 \text{ mA};$ $I_B = -20 \text{ mA}$	[1]	-	-50	-100	mV
		$I_C = -500 \text{ mA};$ $I_B = -50 \text{ mA}$	<u>[1]</u>	-	-200	-300	mV
V_{BEsat}	base-emitter saturation voltage	$I_{C} = -1 \text{ A};$ $I_{B} = -100 \text{ mA}$	<u>[1]</u>	-	-1	-1.2	V
t _d	delay time	$V_{CC} = -6 \text{ V};$		-	8	-	ns
t _r	rise time	$I_{\rm C} = -0.5 \text{ A};$		-	282	-	ns
t _{on}	turn-on time	$I_{Bon} = -0.1 \text{ A};$ $I_{Boff} = 0.1 \text{ A}$		-	290	-	ns
t _s	storage time			-	430	-	ns
t _f	fall time			-	300	-	ns
t _{off}	turn-off time			-	730	-	ns
f _T	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$		-	115	-	MHz
C _c	collector capacitance	$V_{CB} = -20 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	10	-	pF
C _e	emitter capacitance	$V_{EB} = -0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	150	-	pF

^[1] Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

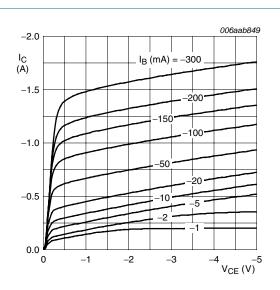
150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor



$$V_{CE} = -10 \text{ V}$$

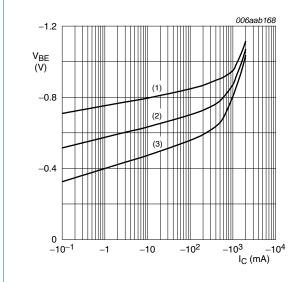
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 4. DC current gain as a function of collector current; typical values



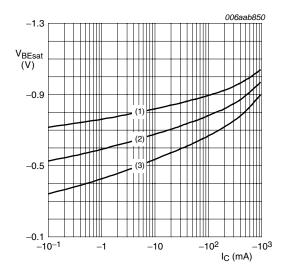
T_{amb} = 25 °C

Fig 5. Collector current as a function of collector-emitter voltage; typical values



- $V_{CE} = -10 \text{ V}$
- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter voltage as a function of collector current; typical values

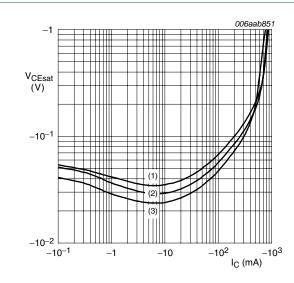


 $I_{\rm C}/I_{\rm B} = 10$

- (1) $T_{amb} = -55$ °C
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Base-emitter saturation voltage as a function of collector current; typical values

150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor



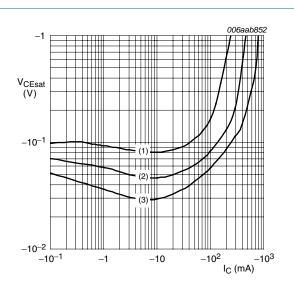
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



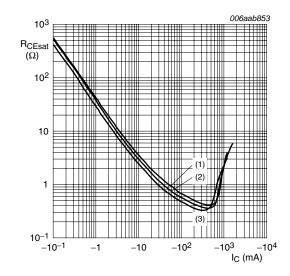
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 50$$

(2)
$$I_C/I_B = 20$$

(3) $I_C/I_B = 10$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



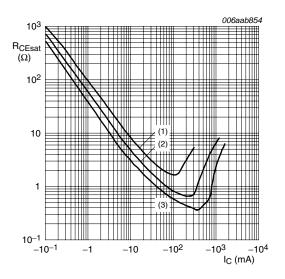
$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 50$$

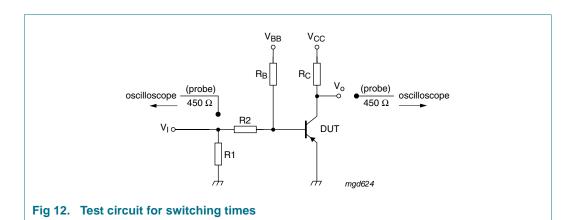
(2) $I_C/I_B = 20$

(3) $I_C/I_B = 10$

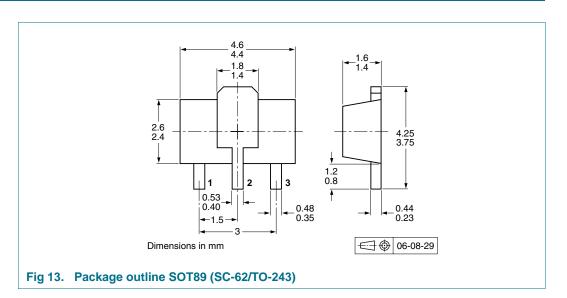
Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values

150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

8. Test information



9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

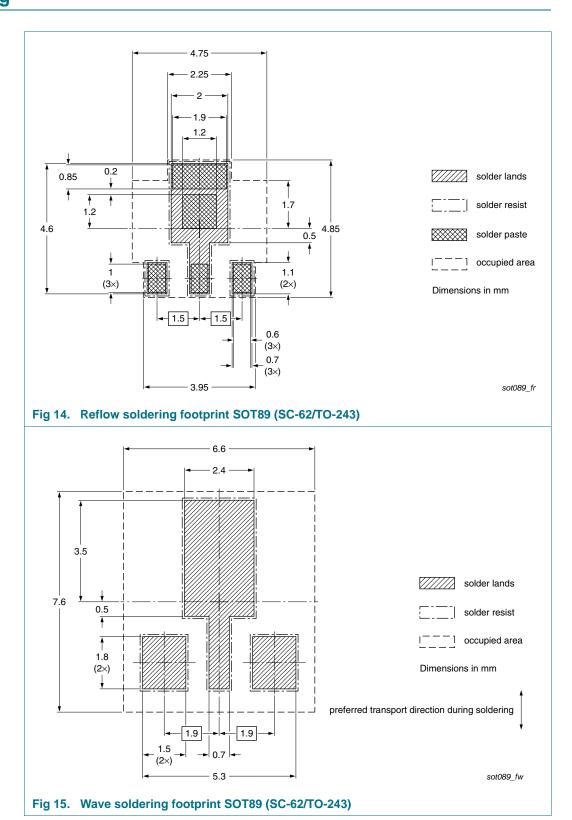
Type number	Package	Description I		Packing quantity	
				1000	4000
PBHV9115X	SOT89	8 mm pitch, 12 mm tape and reel; T1	2]	-115	-135
		8 mm pitch, 12 mm tape and reel; T3	3]	-120	-

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T3: 90° taping

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150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

11. Soldering



150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9115X_1	20100310	Product data sheet	-	-

150 V, 1 A PNP high-voltage low V_{CEsat} (BISS) transistor

13. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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